

GSM2367AS

20V P-Channel Enhancement Mode MOSFET

Product Description

GSM2367AS, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

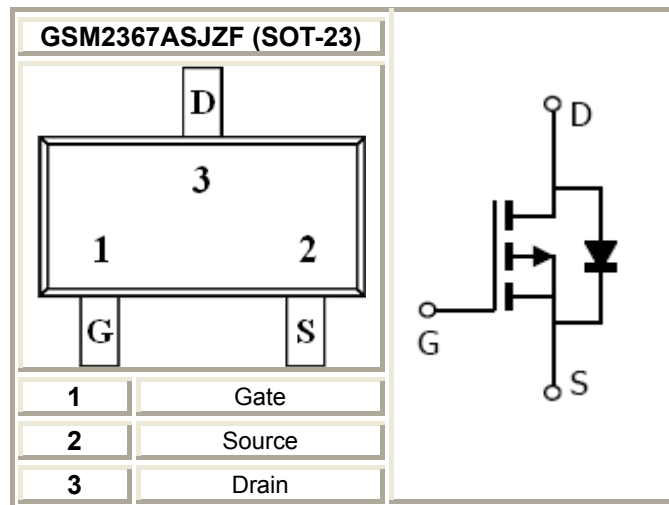
Features

- $-20V/-2.8A, R_{DS(ON)}=80m\Omega@V_{GS}=-4.5V$
- $-20V/-2.5A, R_{DS(ON)}=98m\Omega@V_{GS}=-2.5V$
- $-20V/-2.2A, R_{DS(ON)}=130m\Omega@V_{GS}=-1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

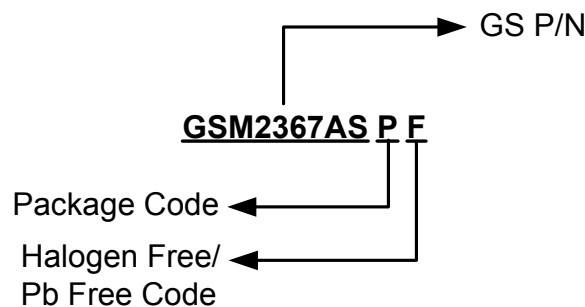
Applications

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Net Working System

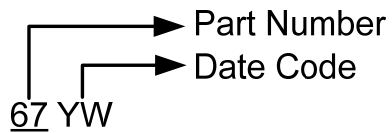
Packages & Pin Assignments



Ordering Information



Marking Information



Part Number	Package	Part Marking
GSM2367ASJZF	SOT-23	<u>67</u> YW

Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

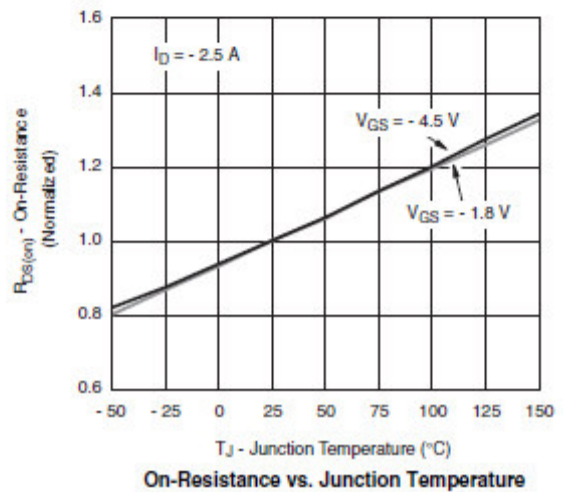
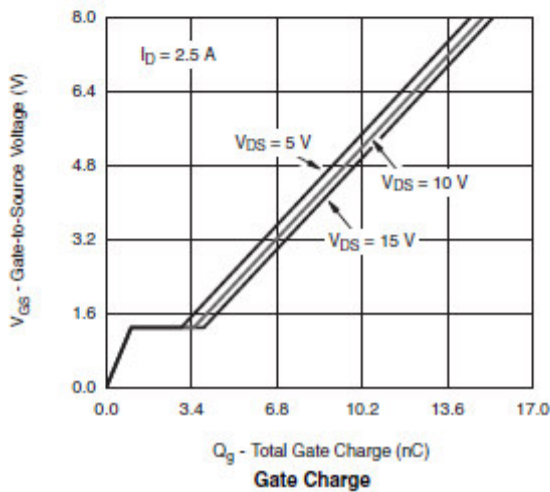
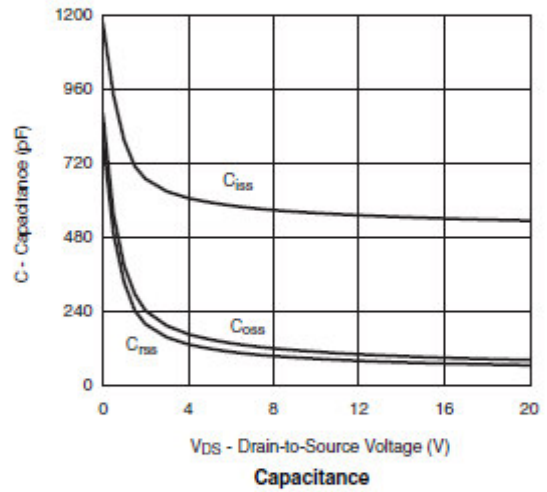
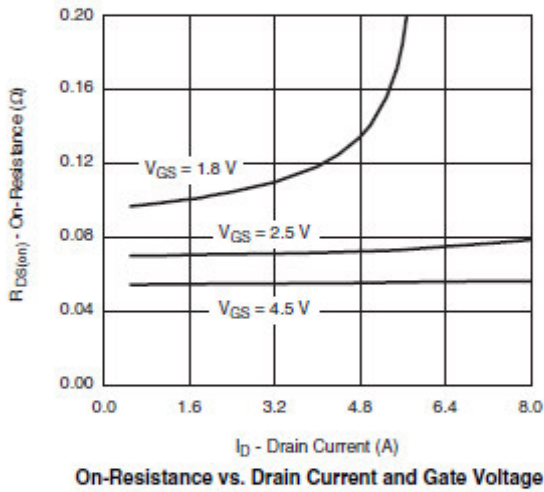
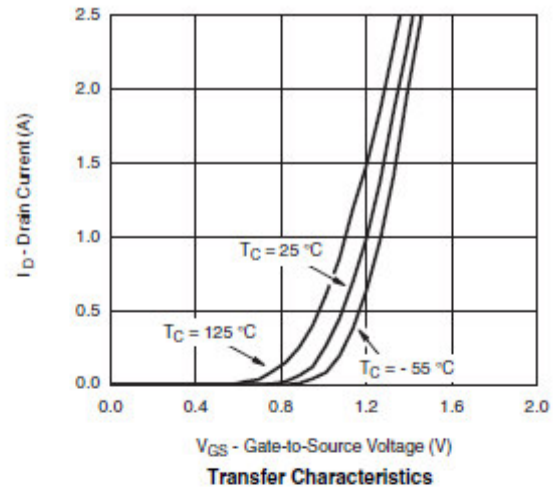
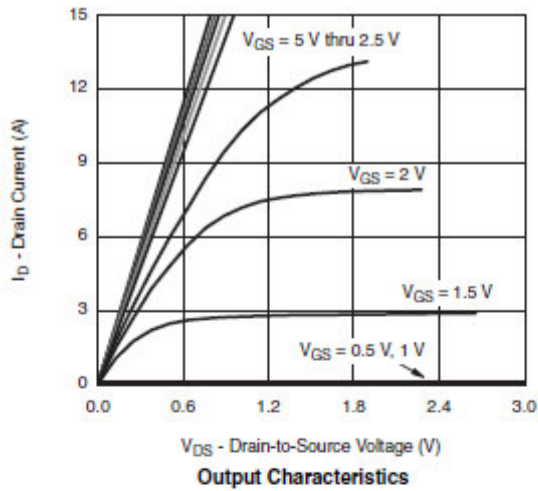
Symbol	Parameter	Typical	Unit	
V _{DSS}	Drain-Source Voltage	-20	V	
V _{GSS}	Gate -Source Voltage	±12	V	
I _D	Continuous Drain Current(T _J =150°C)	T _A =25°C	-2.8	A
		T _A =70°C	-2.2	
I _{DM}	Pulsed Drain Current	-10	A	
I _S	Continuous Source Current(Diode Conduction)	-1.6	A	
P _D	Power Dissipation	T _A =25°C	1.25	W
		T _A =70°C	0.8	
T _J	Operating Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-55/150	°C	
R _{θJA}	Thermal Resistance-Junction to Ambient	120	°C/ W	

Electrical Characteristics

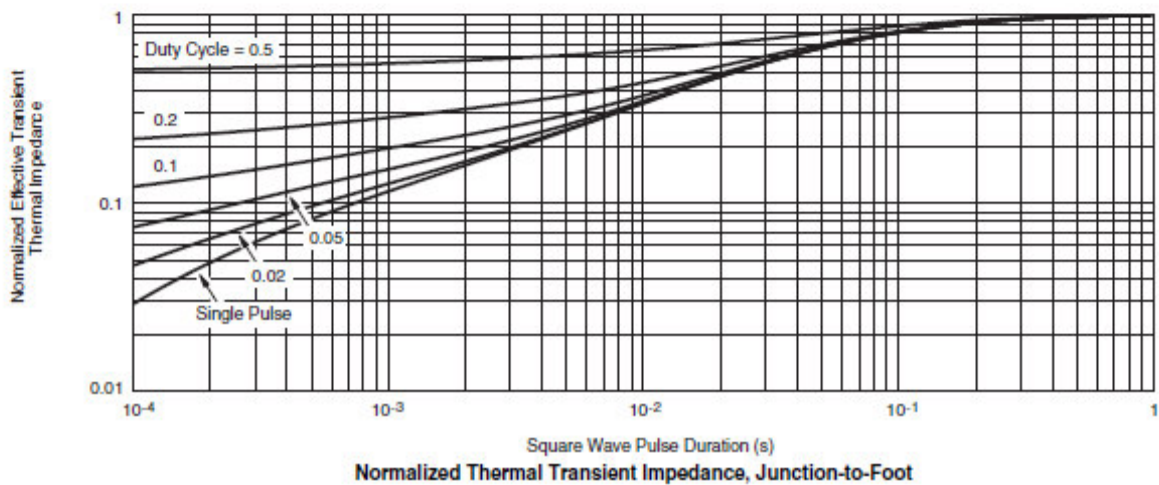
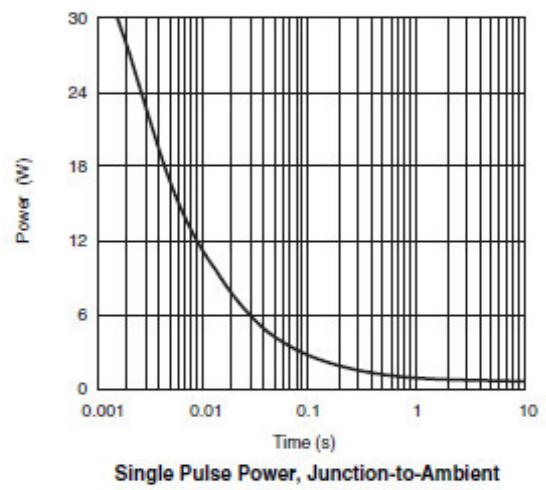
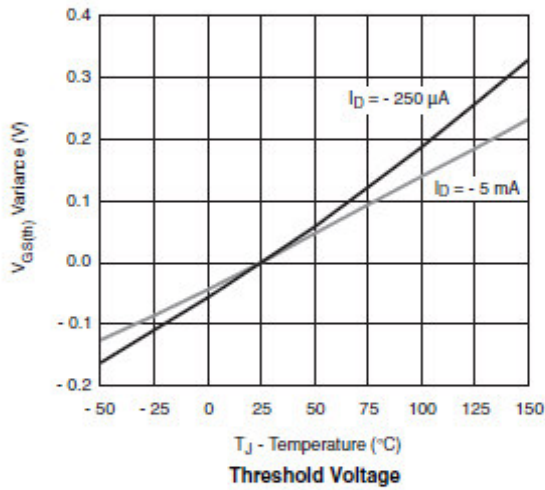
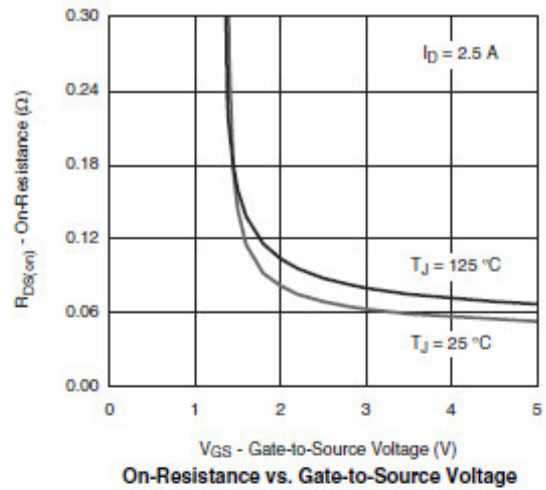
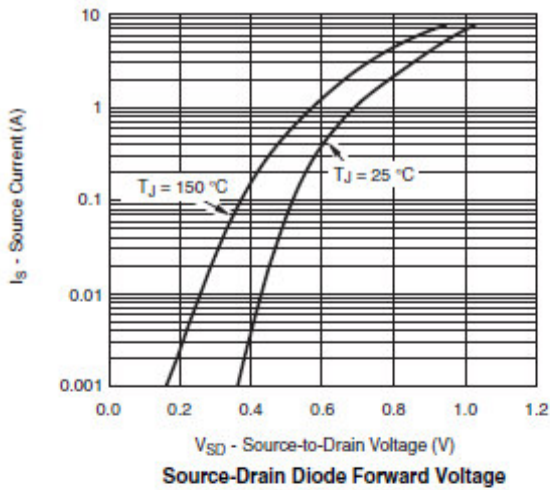
($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ	Max.	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5		-1.0	
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16V, V_{GS}=0V$			-1	μA
		$V_{DS}=-16V, V_{GS}=0V, T_J=85^\circ\text{C}$			-30	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\leq -5V, V_{GS}=-4.5V$	-6			A
		$V_{DS}\leq -5V, V_{GS}=-2.5V$	-3			
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=-4.5V, I_D=-2.8A$		70	80	m Ω
		$V_{GS}=-2.5V, I_D=-2.5A$		88	98	
		$V_{GS}=-1.8V, I_D=-2.2A$		115	130	
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-2.8A$		6.5		S
V_{SD}	Diode Forward Voltage	$I_S=-1.25A, V_{GS}=0V$		-0.75	-1.3	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=-6V, V_{GS}=0V, f=1\text{MHz}$		450		pF
C_{oss}	Output Capacitance			95		
C_{rss}	Reverse Transfer Capacitance			55		
Q_g	Total Gate Charge	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-2.8A$		10	18	nC
Q_{gs}	Gate-Source Charge			1.6		
Q_{gd}	Gate-Drain Charge			3.0		
$t_{d(on)}$	Turn-On Time	$V_{DD}=-6V, R_L=6\Omega, I_D=-1.0A, V_{GEN}=-4.5V, R_G=6\Omega$		8	18	ns
t_r				8	18	
$t_{d(off)}$	Turn-Off Time			25	50	
t_f				25	35	

Typical Performance Characteristics

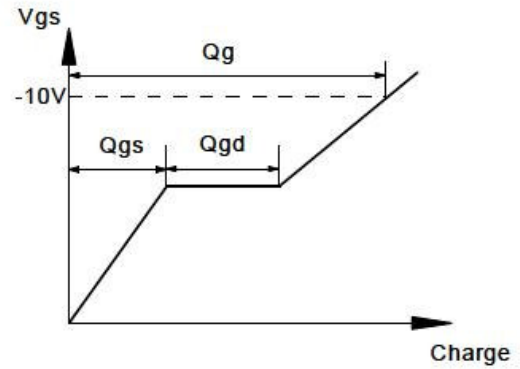
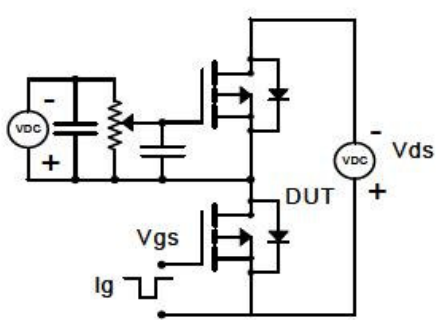


Typical Performance Characteristics (continue)

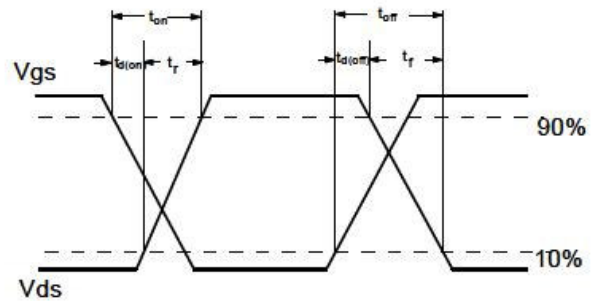
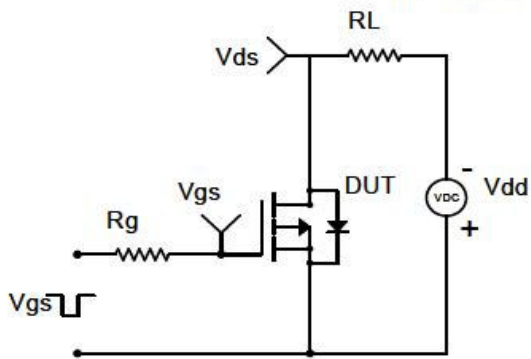


Typical Characteristics

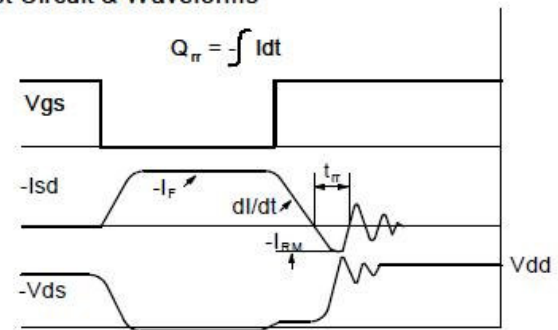
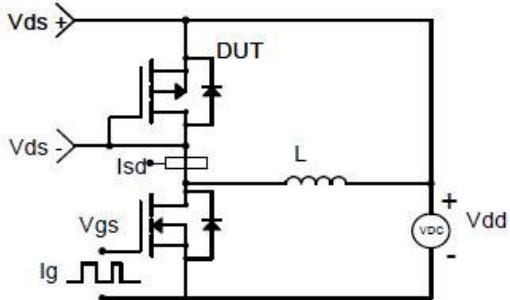
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

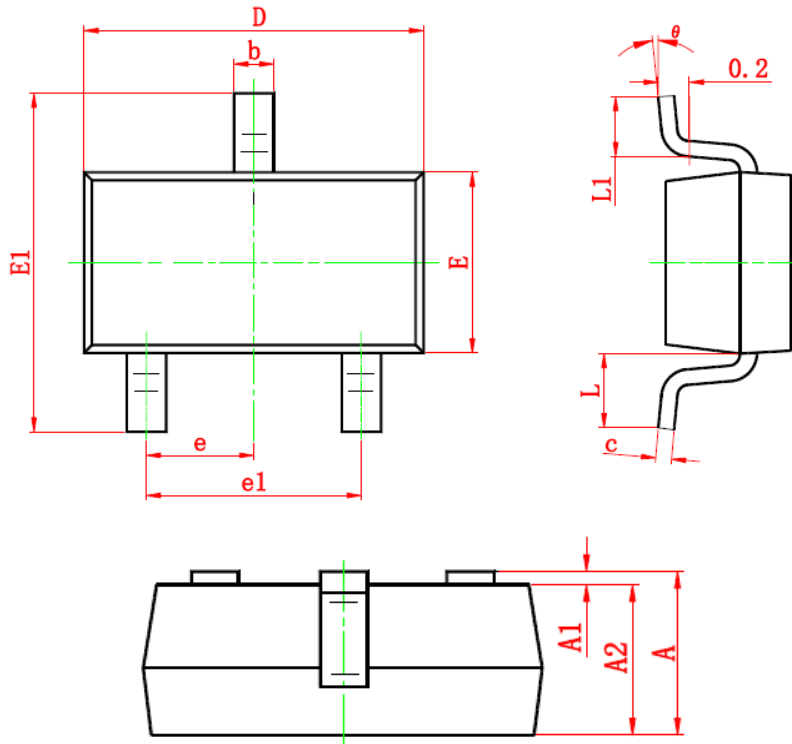


Diode Recovery Test Circuit & Waveforms



Package Dimension

SOT-23







Dimensions





Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°



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